

Abstract

Method for the Production of Transistor Structures with LDD

5 The substrate (1) is etched such that on the source side and on the drain side
downward sloping sidewalls (5) are formed adjacent to the gate electrode (3) and sloping
downward from it. Spacers (7) are positioned there. An implantation (9) of dopant is
performed at a low angle relative to the upper surface, through the spacers (7), in order to
form the regions (11) of lower dopant concentration, and an implantation (10) of dopant is
10 performed at a high angle relative to the upper surface in order to form the source and
drain regions (12).

Figure 6